

Erratum

Ga-vacancy Activation Under Low Energy Electron Irradiation in GaN-based Materials – ERRATUM

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The acknowledgment that follows should have been included in the published article:

THE CORRECTION

This article was originally published on June 2012 with a mistake. The name of the third author was incorrect. The correct name of the third author is "Lukasz Kilanski."

The authors regret the error.

Reference

Henri Nykänen, Sami Suihkonen, Lucasz Kilanski, Markku Sopanen, and Filip Tuomisto: Ga-vacancy Activation Under Low Energy Electron Irradiation in GaN-based Materials, in *Reliability and Materials Issues of III-V and II-VI Semiconductor Optical and Electron Devices and Materials II*, edited by O. Ueda, M. Fukuda, K. Shiojima, and E. Piner (Mater. Res. Soc. Symp. Proc. **1432**, Warrendale, PA, 2012).